

**AMENDMENTS TO THE SPECIFICATION**

Please amend the specification as shown below.

Please amend the paragraph beginning on page 1, line 6, with the following amended paragraph:

The present invention relates to a semiconductor device having bipolar transistors and a method of producing the same, and more particularly relates to a semiconductor device having heterojunction bipolar transistors and a method of producing the same.

Please amend the paragraph beginning on page 7, line 6, with the following amended paragraph:

To achieve the above object, according to a first aspect of the present invention, there is provided a semiconductor device having a semiconductor mesa portion formed on a substrate, including a stack of at least a collector layer, a base layer, and an emitter layer formed in a narrower region compared with the base layer, and functioning as an active region of a bipolar transistor; a base contact pad mesa portion formed on the substrate apart from the semiconductor mesa portion and formed with a height the same as the height of the top surface of the base layer; and a conductive layer formed integrally with a base electrode formed connected to the base layer at part of a region of formation of the base layer other than the region of formation of the emitter layer, a base contact pad electrode formed above the base contact pad mesa portion in a region other than near the edges of the top surface of the base contact pad mesa portion, and an interconnect for connecting the base electrode and the base contact pad electrode.